

DERWENT-ACC-NO: 2003-655221

DERWENT-WEEK: 200514

COPYRIGHT 2005 DERWENT INFORMATION LTD

TITLE: Cvd apparatus using plasma

INVENTOR: PARK, Y S

PATENT-ASSIGNEE: KOKUSAI ELECTRIC KOREA[KOKZ] , KOOKJE ELECTRIC KOREA CO
LTD [KOOKN]

PRIORITY-DATA: 2001KR-0070914 (November 15, 2001)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES
MAIN-IPC			
KR 450286 B	October 15, 2004	N/A	000
H01L 021/205			
KR 2003040581 A	May 23, 2003	N/A	001
H01L 021/205			

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
KR 450286B	N/A	2001KR-0070914	
November 15, 2001			
KR 450286B	Previous Publ.	KR2003040581	N/A
KR2003040581A	N/A	2001KR-0070914	
November 15, 2001			

INT-CL (IPC): H01L021/205

ABSTRACTED-PUB-NO: KR2003040581A

BASIC-ABSTRACT:

NOVELTY - A CVD(Chemical Vapor Deposition) apparatus using plasma is provided to reduce a deposition time and improve the uniformity of a surface of a wafer by installing a plasma generator in the inside of a process chamber.

DETAILED DESCRIPTION - A boat(300) is installed within a process chamber(200).

A plurality of wafers are loaded into the boat. A shower head(400) is used for injecting a process gas to the wafers loaded into the boat. A plasma generator(500) is installed within the shower head in order to form the process gas injected from the shower head to a state of plasma. The shower head is

installed in the inside of the process chamber. A gas induction space is formed by the shower head and a sidewall of the process chamber. A gas induction portion(600) supplies the process gas into the gas induction space of the shower head.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: CVD APPARATUS PLASMA

DERWENT-CLASS: U11 V05

EPI-CODES: U11-C09B; U11-C09C; V05-F04E; V05-F05C; V05-F05E3; V05-F08D1;

100

